

IN THE SPECIFICATION

Paragraph at page 25, line 5:

Fig. 1(A) is a plan view seen from above showing in outline the constitution of a semiconductor device of a first embodiment, and Fig. 1(B) is a plan view showing an expanded outline of the main parts of one region of (A) in order to illustrate the connection relationship between a wiring pattern and electrode pads, while Fig. 1(C) is a detailed view according to Fig. 1(A) and Fig. 1(D) is a cross sectional view taken on line II-II of Fig. 1(C);

Paragraph at page 25, line 5:

Hence the portions 42X of the wiring patterns 42 having a certain length on or in the vicinity of this boundary is preferably comprised of thicker and / or wider wire. In other word, The portions 42X of the wiring patterns 42 on a boundary and vicinity thereof between a region on the upper side of said semiconductor chip 30 and the base flame 20 are formed wider or more thickly than other portions of said wiring patterns 42. As an example, a rectangular thicker and wider wiring portion 42X is illustrated in detailed Figs. 1(C) and 1(D). The other features illustrated in Figs. 1(C) and 1(D) are labeled by the same reference numerals as in the other figures.